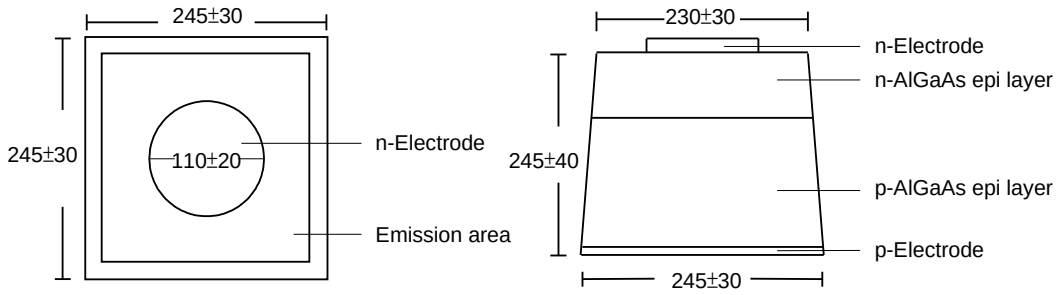
Features :

- N Side Up

Typical Applications :

- Industrial Infrared Equipment

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	245 um x 245±30 um
	Thickness	245±40 um
	Emission area	230±30 um
	Bonding pad	110±20 um
Electrode	Top: N (cathode)	Gold
	Backside: P (anode)	Gold alloy
Surface condition	Smooth	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 20 mA	-	1.39	1.60	V
		I_F = 100 mA	-	1.90	2.20	
Reverse Voltage	V_R	I_R = 10 uA	5	-	-	V
Wavelength	λ_p	I_F = 20 mA	870	880	910	nm
Spectral width at half height	$\triangle\lambda$	I_F = 20 mA	-	70	-	nm
Radiant Power	P_o	I_F = 20 mA	0.3	-	1.0	mW

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

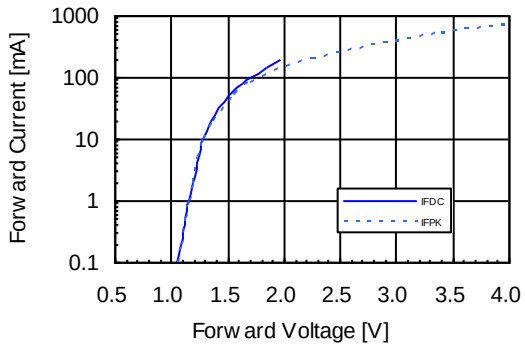


Fig 2. Relative Radiant Power vs. Wavelength

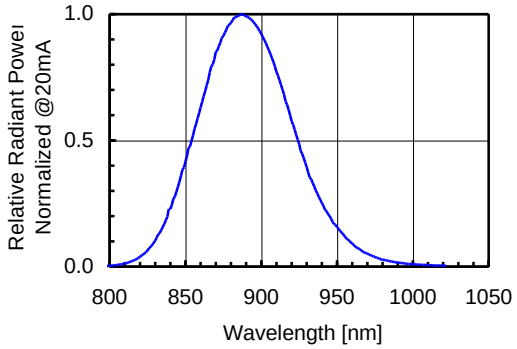


Fig 3. Relative Radiant Power vs. Forward DC Current

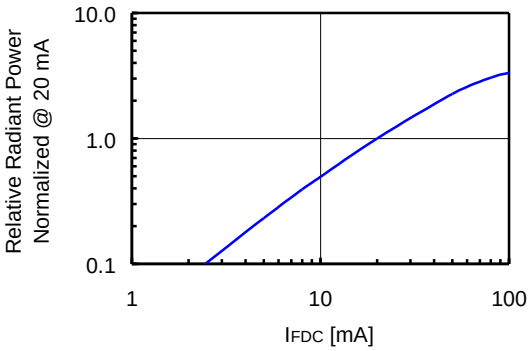


Fig 4. Relative Radiant Power vs. Forward Peak Current

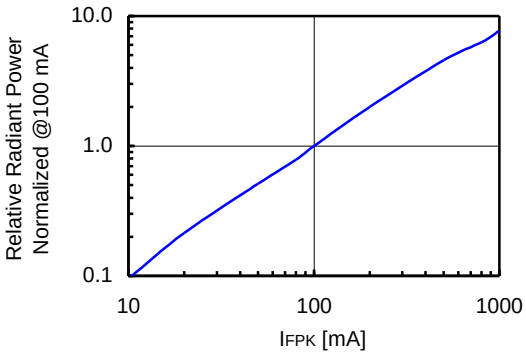


Fig 5. Forward DC Voltage vs. Temperature

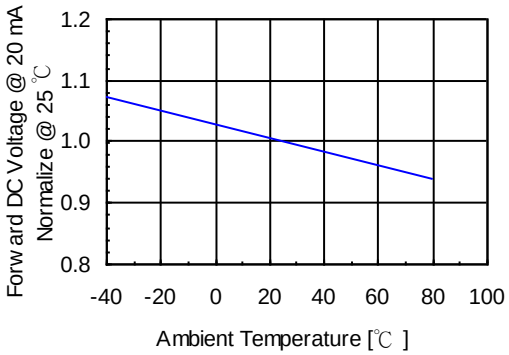


Fig 6. Relative Radiant Power vs. Temperature